



安徽富信半导体科技有限公司

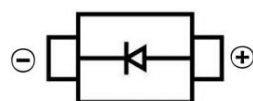
ANHUI FOSAN SEMICONDUCTOR TECHNOLOGY CO., LTD.

S5AB-S5MB

SMB General Purpose Rectifier Diode 通用整流二极管

■Features 特点

Glass passivated junction 玻璃钝化结
 Low reverse leakage current 低反向漏电流
 Low forward voltage drop 低正向压降
 High current capability 高电流能力
 Surface mount device 表面贴装器件
 Case 封装:SMB(DO-214AA)



■Maximum Rating 最大额定值

($T_A=25^{\circ}\text{C}$ unless otherwise noted 如无特殊说明, 温度为 25°C)

Characteristic 特性参数	Symbol 符号	S5 AB	S5 BB	S5 DB	S5 GB	S5 JB	S5 KB	S5 MB	Unit 单位
Marking 印字		S5A	S5B	S5D	S5G	S5J	S5K	S5M	
Peak Reverse Voltage 反向峰值电压	V_{RRM}	50	100	200	400	600	800	1000	V
DC Reverse Voltage 直流反向电压	V_R	50	100	200	400	600	800	1000	V
RMS Reverse Voltage RMS 反向电压	$V_{R(RMS)}$	35	70	140	280	420	560	700	V
Forward Rectified Current 正向整流电流	I_F	5							A
Peak Surge Current 峰值浪涌电流	I_{FSM}	120							A
Thermal Resistance J-A 结到环境热阻	$R_{\theta JA}$	13							$^{\circ}\text{C}/\text{W}$
Junction and Storage Temperature 结温和储藏温度	T_J, T_{stg}	150 $^{\circ}\text{C}$, -55to+150 $^{\circ}\text{C}$							

■Electrical Characteristics 电特性

($T_A=25^{\circ}\text{C}$ unless otherwise noted 如无特殊说明, 温度为 25°C)

Characteristic 特性参数	Symbol 符号	Min 最小值	Typ 典型值	Max 最大值	Unit 单位	Condition 条件
Forward Voltage 正向电压	V_F		1.0	1.1	V	$I_F=5\text{A}$
Reverse Current 反向电流	I_R	(T _A =25 $^{\circ}\text{C}$)		5	uA	$V_R=V_{RRM}$
		(T _A =125 $^{\circ}\text{C}$)		250		
Diode Capacitance 二极管电容	C_D		60		pF	$V_R=4\text{V}, f=1\text{MHz}$



■ Typical Characteristic Curve 典型特性曲线

FIG.1-TYPICAL FORWARD CHARACTERISTICS

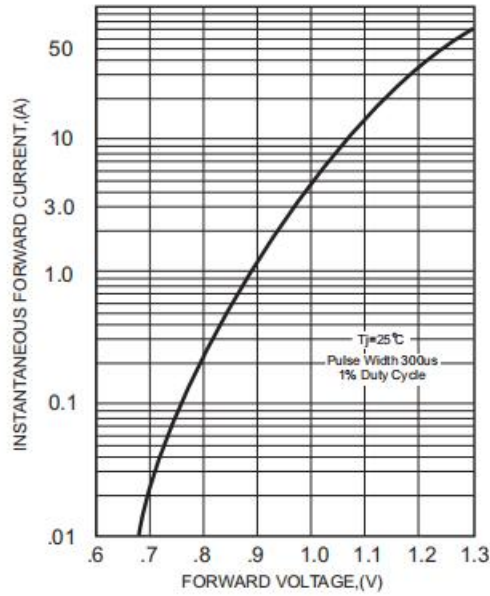


FIG.2-TYPICAL FORWARD CURRENT DERATING CURVE

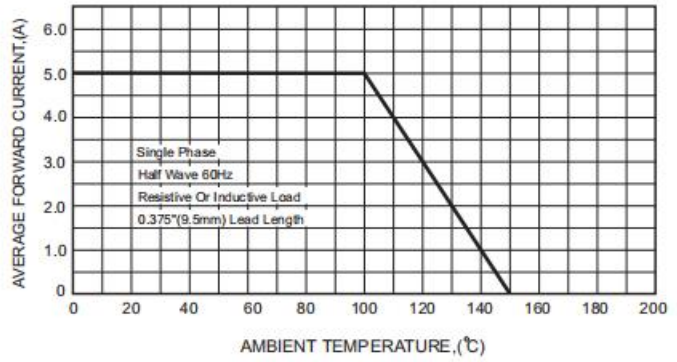


FIG.4-MAXIMUM NON-REPETITIVE FORWARD SURGE CURRENT

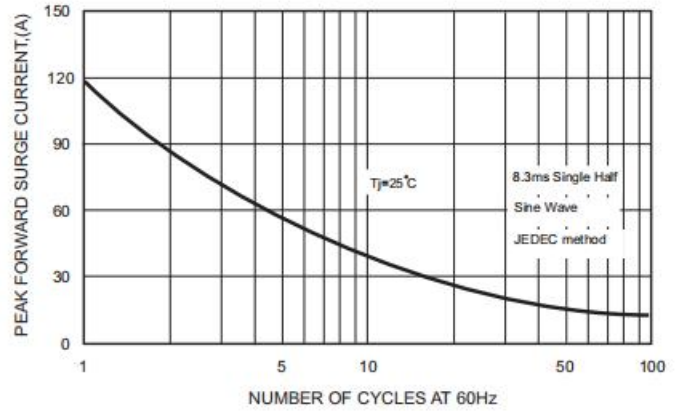


FIG.3 - TYPICAL REVERSE CHARACTERISTICS

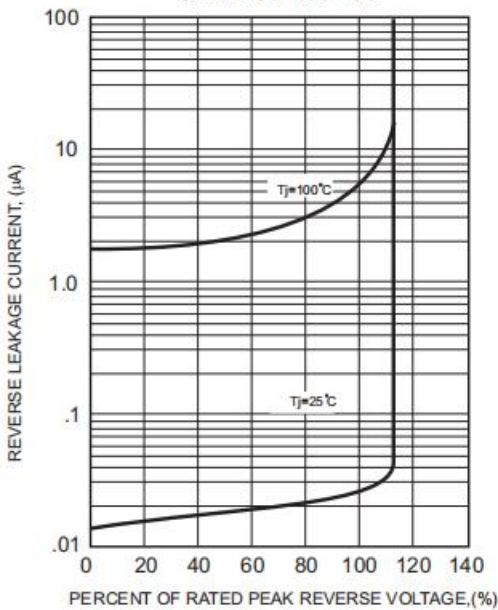
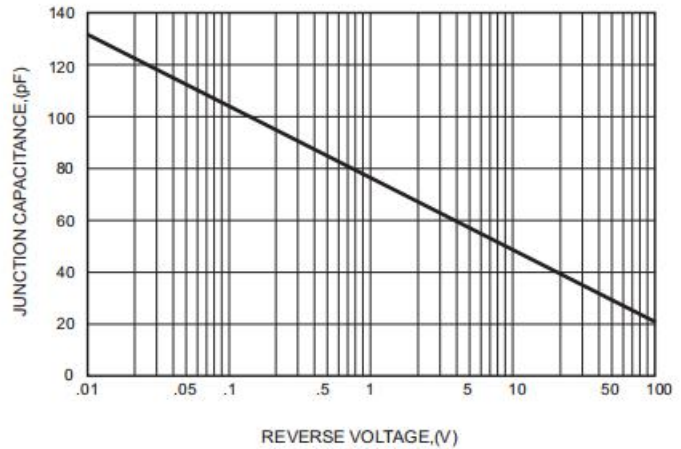
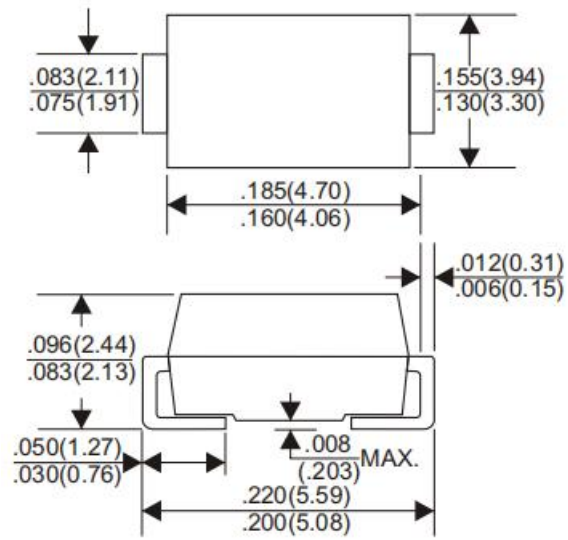


FIG.5-TYPICAL JUNCTION CAPACITANCE



■Dimension 外形封装尺寸

DO-214AA(SMB)



Dimensions in inches and (millimeters)